

## P-Channel NexFET™ Power MOSFET

Check for Samples: [CSD25303W1015](#)

### FEATURES

- Ultra Low Qg and Qgd
- Small Footprint
- Low Profile 0.62mm Height
- Pb Free
- RoHS Compliant
- Halogen Free
- CSP 1 × 1.5 mm Wafer Level Package

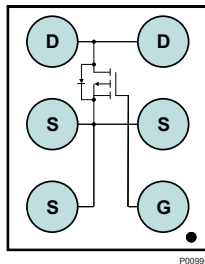
### APPLICATIONS

- Battery Management
- Load Switch
- Battery Protection

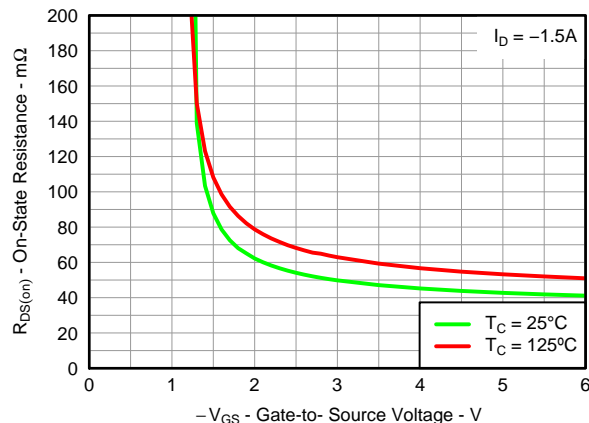
### DESCRIPTION

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra low profile.

Top View



P0099-01

R<sub>DS(ON)</sub> vs V<sub>GS</sub>


### PRODUCT SUMMARY

| T <sub>A</sub> = 25°C unless otherwise stated |                               | TYPICAL VALUE           | UNIT  |
|---|-------------------------------|-------------------------|-------|
| V <sub>DS</sub>                               | Drain to Source Voltage       | -20                     | V     |
| Q <sub>g</sub>                                | Gate Charge Total (4.5V)      | 3.3                     | nC    |
| Q <sub>gd</sub>                               | Gate Charge Gate to Drain     | 0.6                     | nC    |
| R <sub>DS(on)</sub>                           | Drain to Source On Resistance | V <sub>GS</sub> = -1.8V | 72 mΩ |
|   |                               | V <sub>GS</sub> = -2.5V | 56 mΩ |
|   |                               | V <sub>GS</sub> = -4.5V | 46 mΩ |
| V <sub>GS(th)</sub>                           | Voltage Threshold             | -0.65                   | V     |

### ORDERING INFORMATION

| Device        | Package                     | Media       | Qty  | Ship          |
|---------------|-----------------------------|-------------|------|---------------|
| CSD25303W1015 | 1 × 1.5 Wafer Level Package | 7-inch reel | 3000 | Tape and Reel |

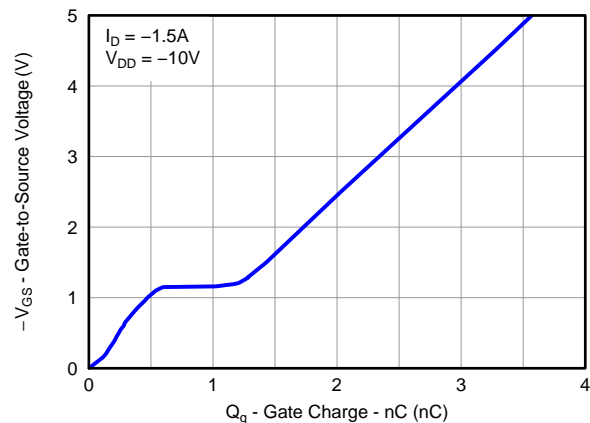
### ABSOLUTE MAXIMUM RATINGS

| T <sub>A</sub> = 25°C unless otherwise stated |  | VALUE      | UNIT |
|---|--|------------|------|
| V <sub>DS</sub>                               | Drain to Source Voltage  | -20        | V    |
| V <sub>GS</sub>                               | Gate to Source Voltage   | ±8         | V    |
| I <sub>D</sub>                                | Continuous Drain Current, T <sub>C</sub> = 25°C <sup>(1)</sup> | -3         | A    |
| I <sub>DM</sub>                               | Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>     | -9         | A    |
| P <sub>D</sub>                                | Power Dissipation <sup>(1)</sup>                               | 1.5        | W    |
| T <sub>STG</sub>                              | Storage Temperature Range                                      | -55 to 150 | °C   |
| T <sub>J</sub>                                | Operating Junction Temperature Range                           |            |      |

(1) Typical R<sub>θJA</sub> = 90°C/W on 1in<sup>2</sup> Cu (2 oz.) on 0.060" thick FR4 PCB.

(2) Pulse width ≤1ms, duty cycle ≤2%

Gate Charge



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## ELECTRICAL CHARACTERISTICS

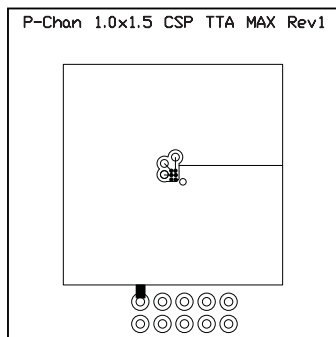
( $T_A = 25^\circ\text{C}$  unless otherwise stated)

| PARAMETER               |                                  | TEST CONDITIONS  | MIN   | TYP   | MAX  | UNIT |
|-------------------------|----------------------------------|--|-------|-------|------|------|
| Static Characteristics  |                                  |  |       |       |      |      |
| BV <sub>DSS</sub>       | Drain to Source Voltage          | V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA  | -20   |       |      | V    |
| I <sub>DSS</sub>        | Drain to Source Leakage Current  | V <sub>GS</sub> = 0V, V <sub>DS</sub> = -16V   |       |       | -1   | μA   |
| I <sub>GSS</sub>        | Gate to Source Leakage Current   | V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±8V  |       |       | -100 | nA   |
| V <sub>GS(th)</sub>     | Gate to Source Threshold Voltage | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA                                    | -0.4  | -0.65 | -1   | V    |
| R <sub>DS(on)</sub>     | Drain to Source On Resistance    | V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -1.5A  |       | 72    | 92   | mΩ   |
|                         |                                  | V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -1.5A  |       | 56    | 71   | mΩ   |
|                         |                                  | V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.5A  |       | 46    | 58   | mΩ   |
| g <sub>fs</sub>         | Transconductance                 | V <sub>DS</sub> = -10V, I <sub>D</sub> = -1.5A   |       | 9.6   |      | S    |
| Dynamic Characteristics |                                  |  |       |       |      |      |
| C <sub>ISS</sub>        | Input Capacitance                | V <sub>GS</sub> = 0V, V <sub>DS</sub> = -10V, f = 1MHz   |       | 335   | 435  | pF   |
| C <sub>OSS</sub>        | Output Capacitance               |  |       | 149   | 191  | pF   |
| C <sub>RSS</sub>        | Reverse Transfer Capacitance     |  |       | 50    | 65   | pF   |
| R <sub>g</sub>          |                                  |  |       | 0.6   | 1.2  | Ω    |
| Q <sub>g</sub>          | Gate Charge Total (-4.5V)        | V <sub>DS</sub> = -10V, I <sub>D</sub> = -1.5A   |       | 3.3   | 4.3  | nC   |
| Q <sub>gd</sub>         | Gate Charge Gate to Drain        |  |       | 0.6   |      | nC   |
| Q <sub>gs</sub>         | Gate Charge Gate to Source       |  |       | 0.6   |      | nC   |
| Q <sub>g(th)</sub>      | Gate Charge at V <sub>th</sub>   |  |       | 0.3   |      | nC   |
| Q <sub>OSS</sub>        | Output Charge                    | V <sub>DS</sub> = -11V, V <sub>GS</sub> = 0V   |       | 2.5   |      | nC   |
| t <sub>d(on)</sub>      | Turn On Delay Time               | V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.5A<br>R <sub>G</sub> = 4Ω |       | 3.9   |      | ns   |
| t <sub>r</sub>          | Rise Time                        |  |       | 8.6   |      | ns   |
| t <sub>d(off)</sub>     | Turn Off Delay Time              |  |       | 11.3  |      | ns   |
| t <sub>f</sub>          | Fall Time                        |  |       | 7.8   |      | ns   |
| Diode Characteristics   |                                  |  |       |       |      |      |
| V <sub>SD</sub>         | Diode Forward Voltage            | I <sub>S</sub> = -1.5A, V <sub>GS</sub> = 0V   | -0.72 |       | -1   | V    |
| Q <sub>rr</sub>         | Reverse Recovery Charge          | V <sub>dd</sub> = -11V, I <sub>F</sub> = -1.5A, di/dt = 200A/μs                                |       | 3.6   |      | nC   |
| t <sub>rr</sub>         | Reverse Recovery Time            |  |       | 11.3  |      | ns   |

## THERMAL CHARACTERISTICS

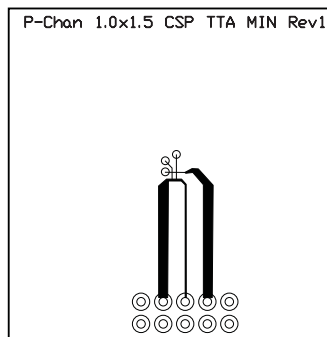
( $T_A = 25^\circ\text{C}$  unless otherwise stated)

| PARAMETER       |  | MIN | TYP | MAX | UNIT               |
|-----------------|--|-----|-----|-----|--------------------|
| $R_{\theta JA}$ | Thermal Resistance Junction to Ambient (Minimum Cu area)           |     |     | 198 | $^\circ\text{C/W}$ |
|                 | Thermal Resistance Junction to Ambient (1 in <sup>2</sup> Cu area) |     |     | 112 | $^\circ\text{C/W}$ |



M0155-01

Max  $R_{\theta JA} = 112^{\circ}\text{C/W}$   
when mounted on 1  
 $\text{inch}^2$  of 2 oz. Cu.

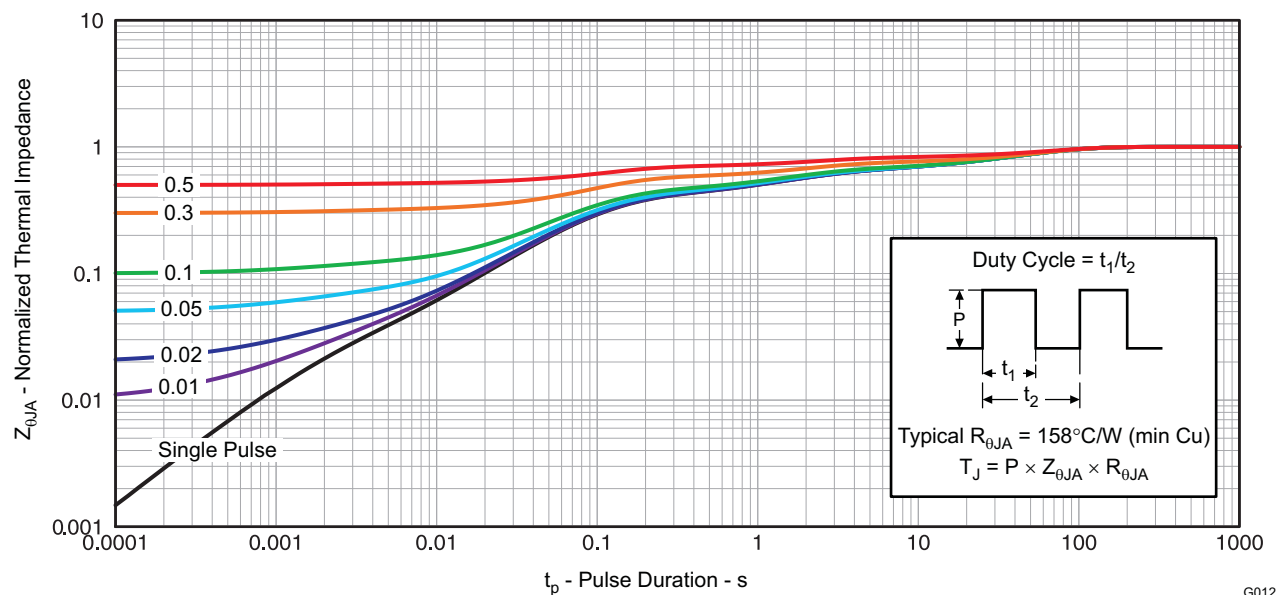


M0156-01

Max  $R_{\theta JA} = 198^{\circ}\text{C/W}$   
when mounted on  
minimum pad area of 2  
oz. Cu.

## TYPICAL MOSFET CHARACTERISTICS

( $T_A = 25^{\circ}\text{C}$  unless otherwise stated)



G012

Figure 1. Transient Thermal Impedance

## TYPICAL MOSFET CHARACTERISTICS (continued)

( $T_A = 25^\circ\text{C}$  unless otherwise stated)

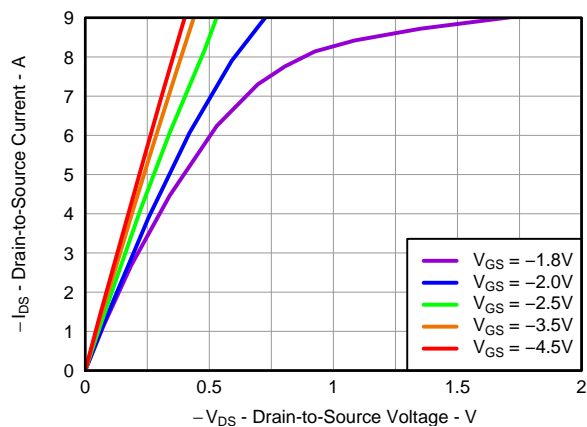


Figure 2. Saturation Characteristics

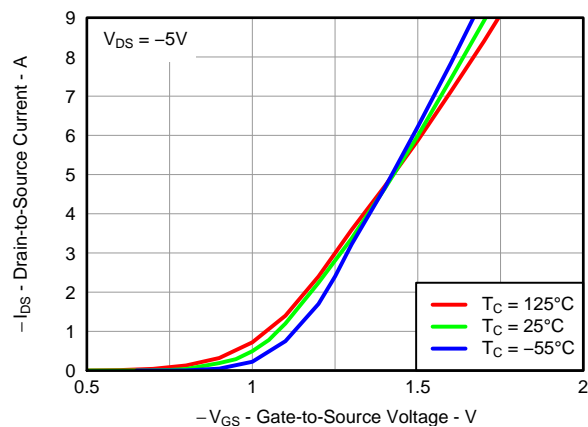


Figure 3. Transfer Characteristics

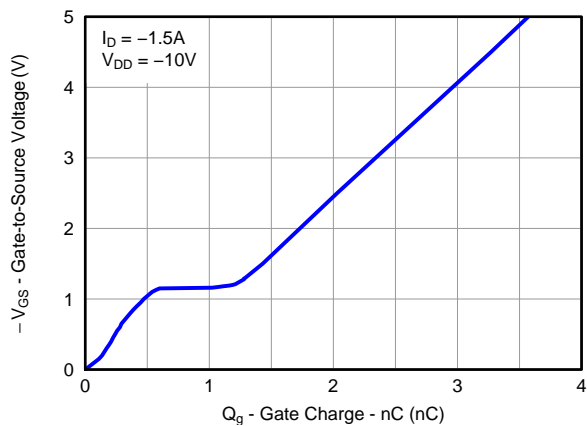


Figure 4. Gate Charge

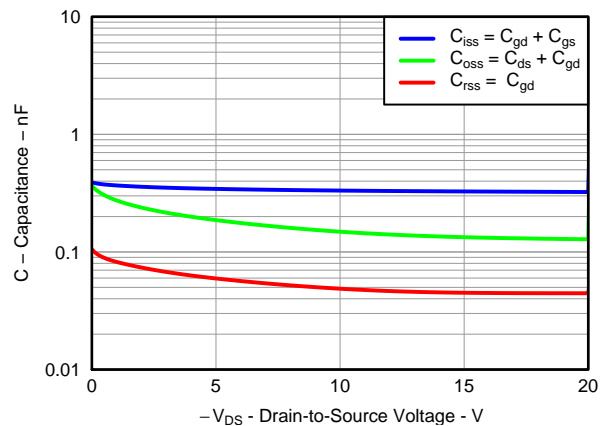


Figure 5. Capacitance

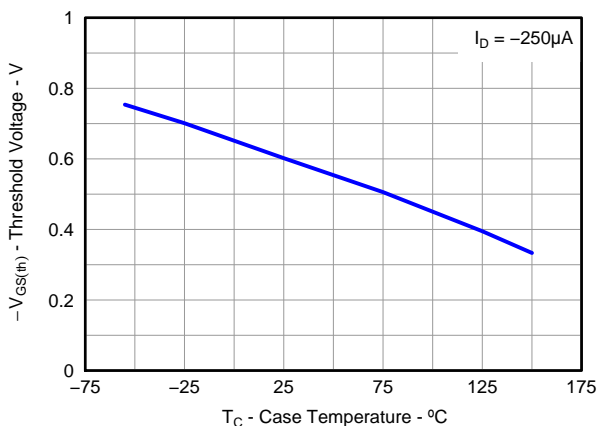


Figure 6. Threshold Voltage vs. Temperature

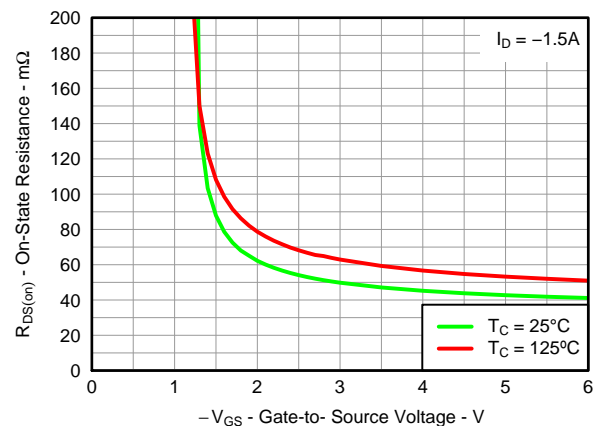


Figure 7. On Resistance vs. Gate Voltage

## TYPICAL MOSFET CHARACTERISTICS (continued)

( $T_A = 25^\circ\text{C}$  unless otherwise stated)

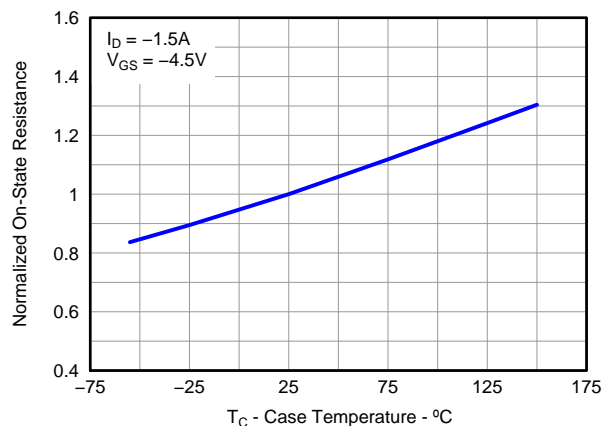


Figure 8. On Resistance vs. Temperature

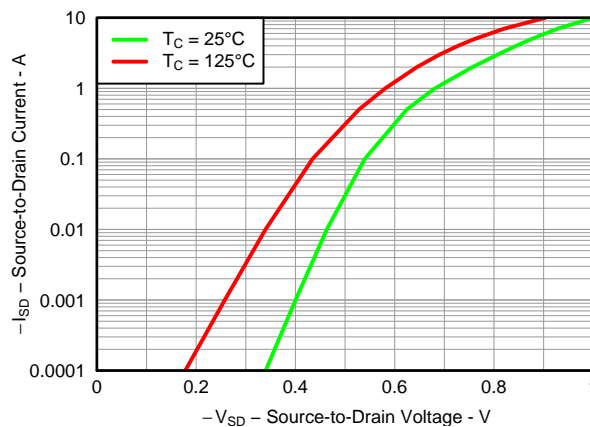


Figure 9. Typical Diode Forward Voltage

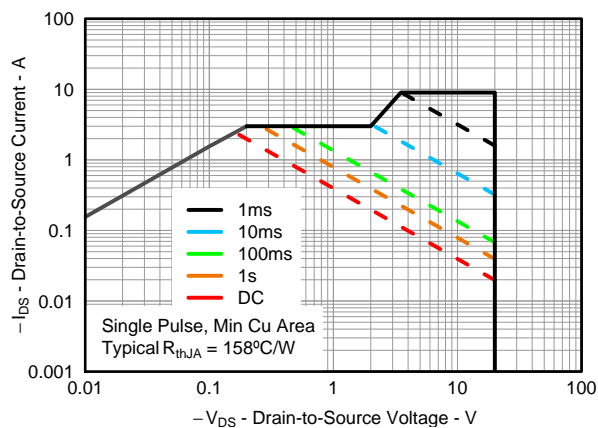


Figure 10. Maximum Safe Operating Area

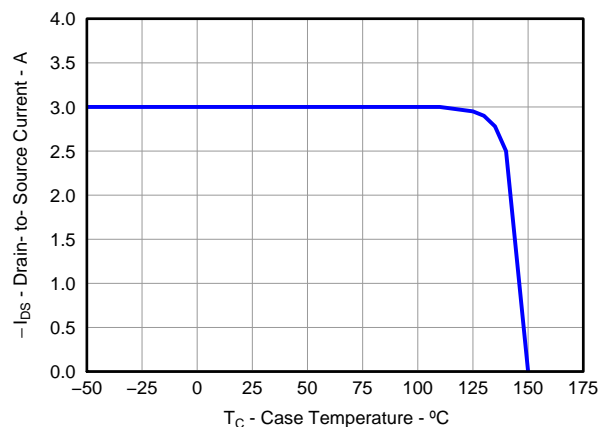
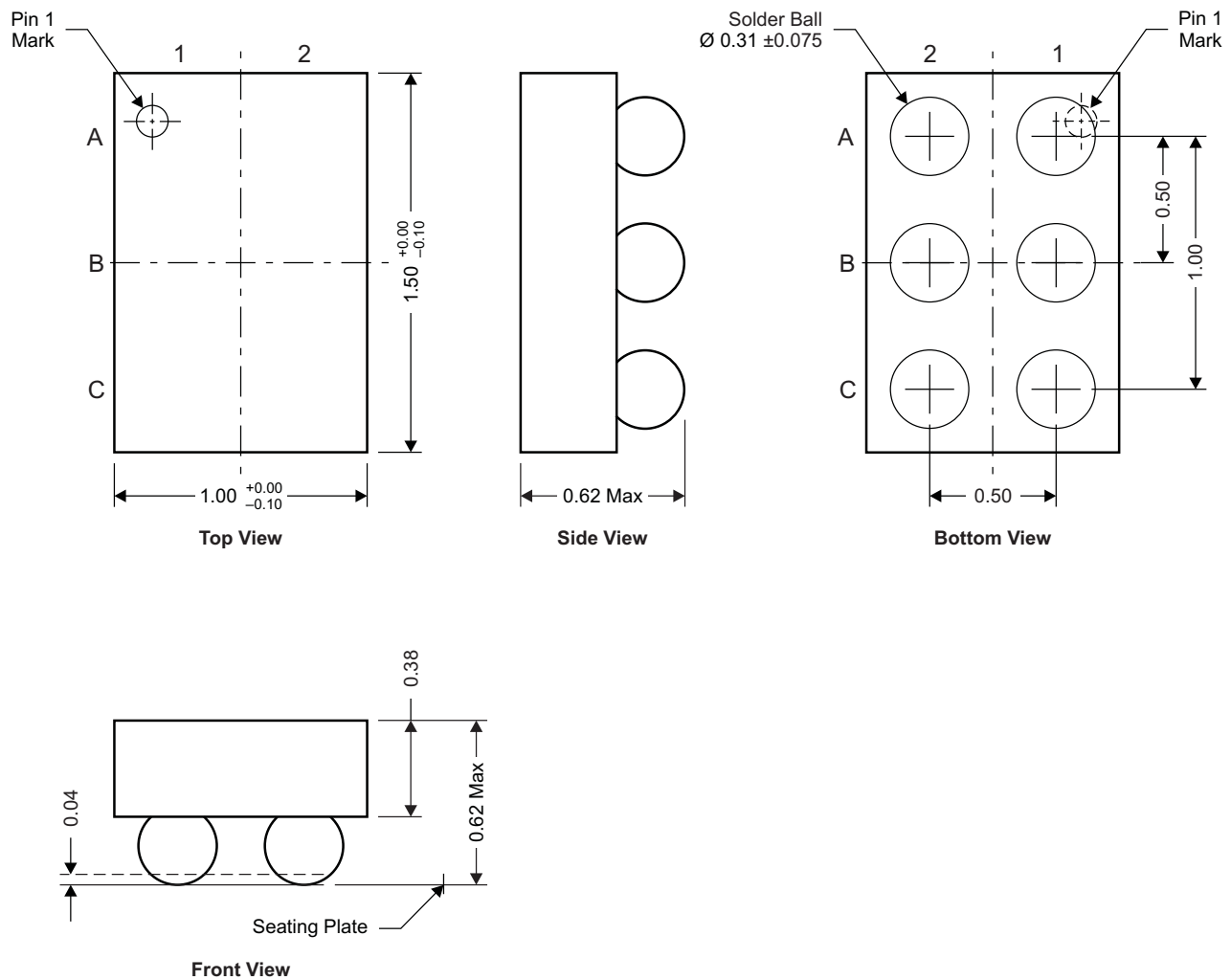


Figure 11. Maximum Drain Current vs. Temperature

## MECHANICAL DATA

### CSD25303W1015 Package Dimensions



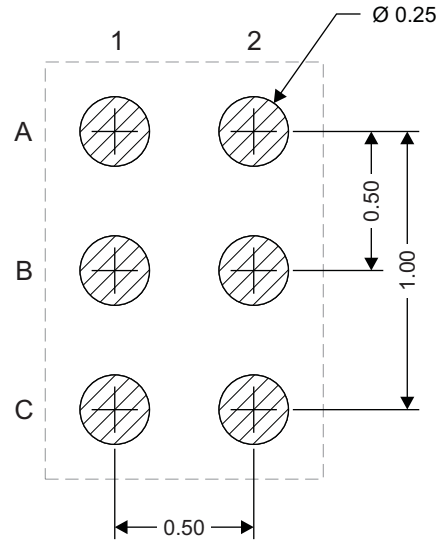
NOTE: All dimensions are in mm (unless otherwise specified)

M0157-01

### Pinout

| POSITION   | DESIGNATION |
|------------|-------------|
| C1, C2     | Drain       |
| A1         | Gate        |
| A2, B1, B2 | Source      |

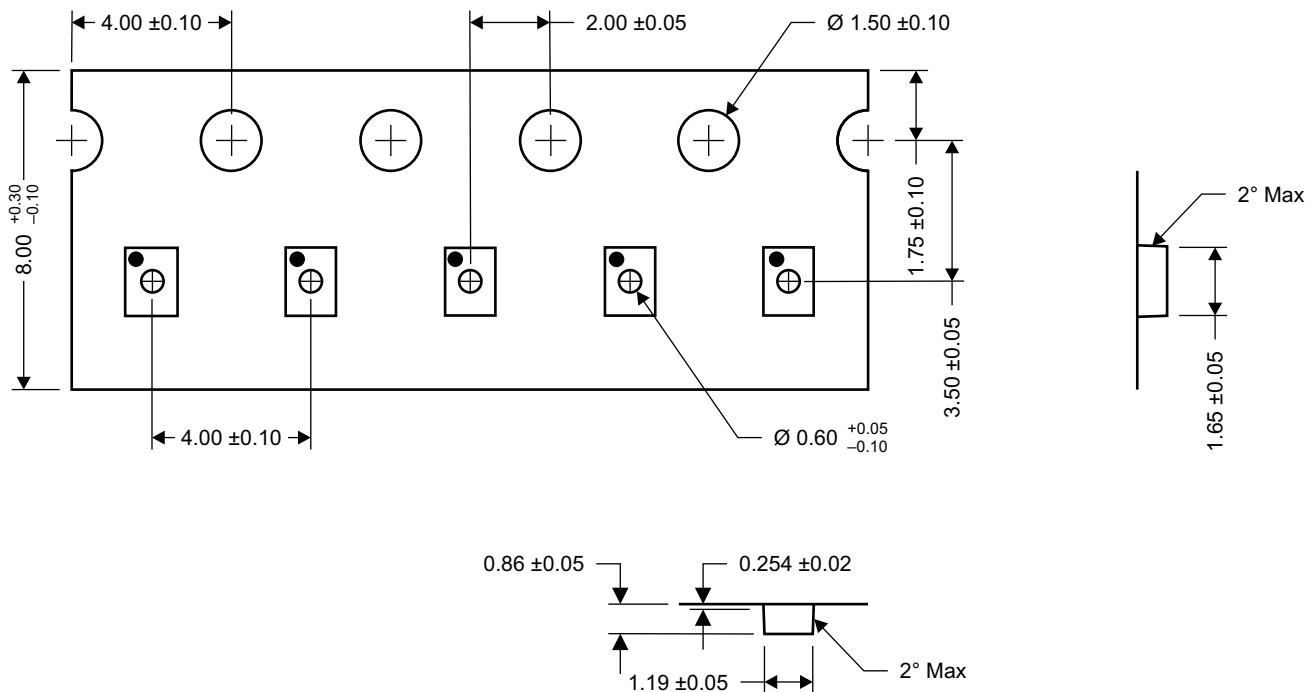
## Land Pattern Recommendation



M0158-01

NOTE: All dimensions are in mm (unless otherwise specified)

## Tape and Reel Information



M0159-01

NOTE: All dimensions are in mm (unless otherwise specified)

## PACKAGING INFORMATION

| Orderable Device | Status<br>(1) | Package Type | Package<br>Drawing | Pins | Package<br>Qty | Eco Plan<br>(2)            | Lead/Ball Finish<br>(6) | MSL Peak Temp<br>(3) | Op Temp (°C) | Device Marking<br>(4/5) | Samples |
|------------------|---------------|--------------|--------------------|------|----------------|----------------------------|-------------------------|----------------------|--------------|-------------------------|---------|
| CSD25303W1015    | LIFEBUY       | DSBGA        | YZC                | 6    | 3000           | Green (RoHS<br>& no Sb/Br) | SNAGCU                  | Level-1-260C-UNLIM   | -55 to 150   |                         |         |

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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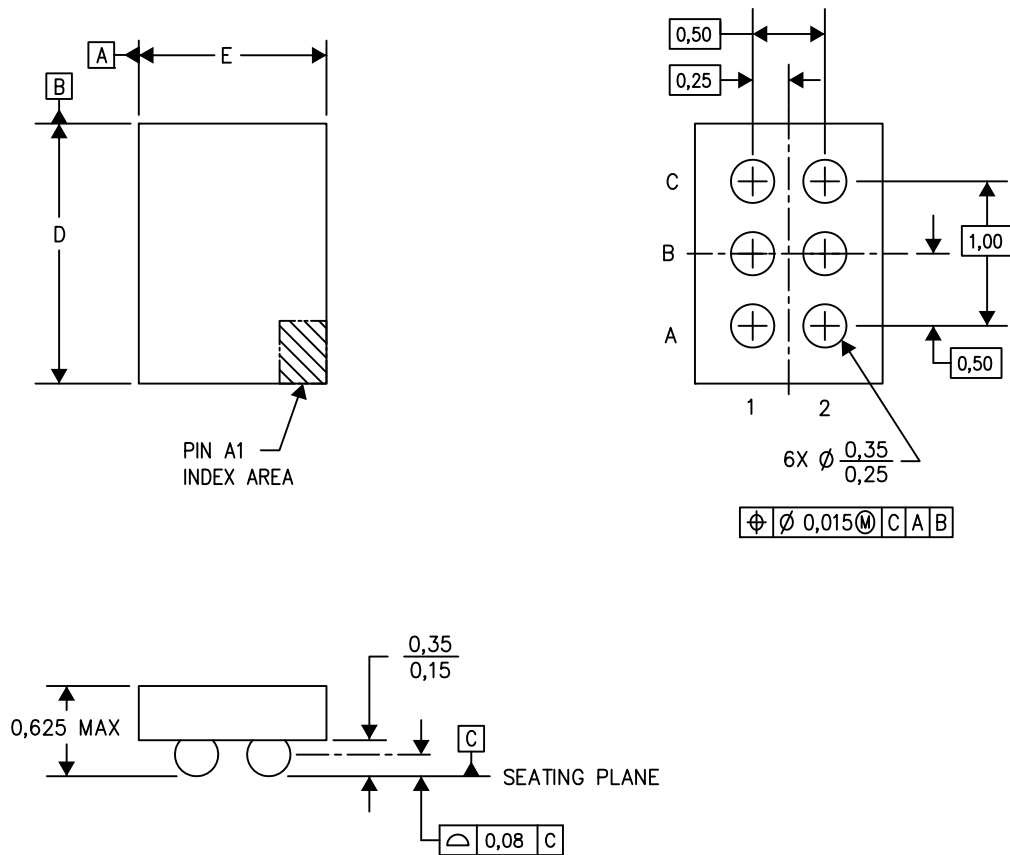
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YZC (R-XBGA-N6)

DIE-SIZE BALL GRID ARRAY



4205056/E 07/13

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. NanoFree™ package configuration.

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|                              |  |
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### Applications

|                               |  |
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| Computers and Peripherals     | <a href="http://www.ti.com/computers">www.ti.com/computers</a>                           |
| Consumer Electronics          | <a href="http://www.ti.com/consumer-apps">www.ti.com/consumer-apps</a>                   |
| Energy and Lighting           | <a href="http://www.ti.com/energy">www.ti.com/energy</a>                                 |
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